KINETICS OF ISOTHERMAL ANNEALING IN AIR OF OWN UNSTABLE POINT DEFECTS IN EPITAXIAL POLYCRYSTALLINE LEAD TELLURIDE FILMS OF *n*-TYPE

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S u m m a r y

To define the characteristic relaxation time and activation energy of the migration processes of own unstable point defects in *n*-PbTe, the approach of the theory of rates of quasi-chemical reactions and X-ray diffractometry data on isothermal annealing of films in air are used. It is shown that the dominant atomic defects in films are both donor lead interstitials, Pb_i , and acceptor tellurium vacancies, V_{Te}, before annealing and acceptor lead vacancies, V_{Pb}, after annealing in air.